

N-channel 60 V, 5.6 mΩ logic level MOSFET in LFPAK56 3 June 2016

Product data sheet

1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

Features and benefits 2.

- Advanced TrenchMOS provides low R_{DSon} and low gate charge •
- Logic level gate operation
- Avalanche rated, 100% tested •
- LFPAK provides maximum power density in a Power SO8 package

Applications 3.

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- Synchronous rectifier in LLC topology
- Chargers & adaptors with $V_{out} < 10 V$
- Fast charge & USB-PD applications •
- Battery powered motor control
- LED lighting & TV backlight

4. Quick reference data

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	100	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	167	W
Static chara	acteristics	·					
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>		-	5.4	7.2	mΩ
Dynamic cl	naracteristics			1			
Q _{GD}	gate-drain charge	$I_{D} = 25 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 5 \text{ V};$ T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	12	-	nC

[1] Continuous current is limited by package.

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N-channel 60 V, 5.6 mΩ logic level MOSFET in LFPAK56

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
PSMN5R6-60YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN5R6-60YL	5R6L60

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	60	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	60	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	167	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	100	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	72	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	405	А
T _{stg}	storage temperature			-55	175	°C

N-channel 60 V, 5.6 m Ω logic level MOSFET in LFPAK56

Symbol	Parameter	Conditions		Min	Max	Unit
Тj	junction temperature			-55	175	°C
Source-drai	in diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	405	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 100 \text{ A}; \text{V}_{\text{sup}} \leq 60 \text{V}; \text{R}_{\text{GS}} = 50 \Omega; \\ \text{V}_{\text{GS}} &= 5 \text{V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 4} \end{split}$	[2][3]	-	88.2	mJ

[1] Continuous current is limited by package.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.

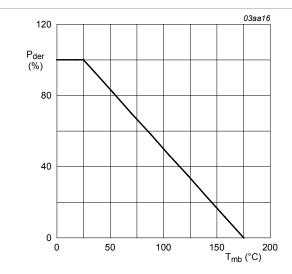
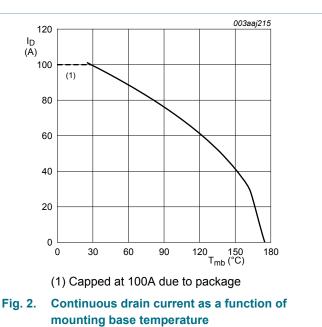


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

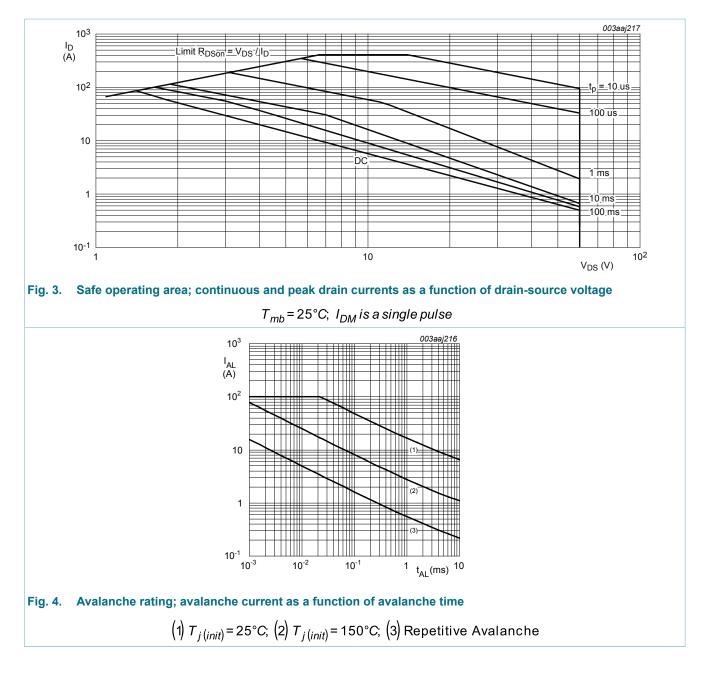
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



 $V_{GS} \ge 5V$

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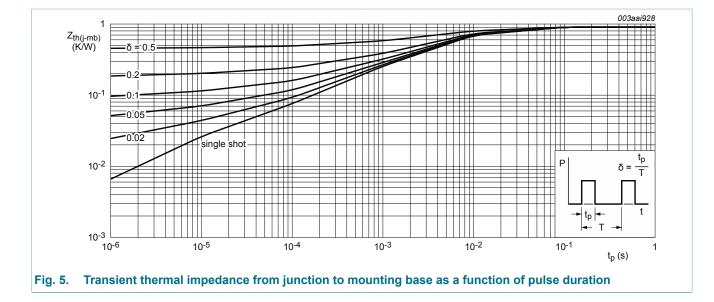
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9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.9	K/W

N-channel 60 V, 5.6 mΩ logic level MOSFET in LFPAK56



10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · · · · · · · · · · · · · · ·	I			
V _{(BR)DSS}	drain-source	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	60	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	54	-	- 2.1 2.45 - 10 500 100 100 7.2 5.6 16.3	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	1.4	1.7	2.1	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 9</u>	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}; Fig. 9$	0.5	- - V 0.05 10 μA - 500 μA 2 100 nA 2 100 nA	V	
I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	2		nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>	-	5.4	7.2	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	4.7	5.6	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	16.3	mΩ
Dynamic cl	naracteristics		1			
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 48 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	66.8	-	nC
		I _D = 25 A; V _{DS} = 48 V; V _{GS} = 5 V;	-	35	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	_	9.5	-	nC

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Qr

recovered charge

function of drain-source voltage; typical values

PSMN5R6-60YL

nC

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N-channel 60 V, 5.6 mΩ logic level MOSFET in LFPAK56

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Q _{GD}	gate-drain charge		-	12	-	nC
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;	-	3769	5026	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	341	409	pF
C _{rss}	reverse transfer capacitance		-	185	253	pF
t _{d(on)}	turn-on delay time	V_{DS} = 45 V; R _L = 1.8 Ω; V _{GS} = 5 V;	-	19.3	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	36.4	-	ns
t _{d(off)}	turn-off delay time	_	-	49.4	-	ns
t _f	fall time	-	-	32.1	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.81	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	23.1	-	ns

300	003aaj219	20					003aa	aj220
		R _{DSon}						
I _D V _{GS} (1	V) = 10 4.5	(mΩ)						
(A)		16					_	
	3.5							
200		10						
		12						
		8						
100	3	8						
	2.8	4			\sim			
	2.6	4						
	2.4							
0		0						
0 1	2 ³ V _{DS} (V) ⁴		0 :	2	4	6	8 V _{GS} (V)	10
T _j = 25 °C; t _p = 300 µ	µs	Fig. 7. Drai	n-sourc	e on-st	ate resi	stanc	e as a f	unction
Fig. 6. Output characteris	tics; drain current as a	of g	ate-sou	rce volt	age; ty	pical	values	

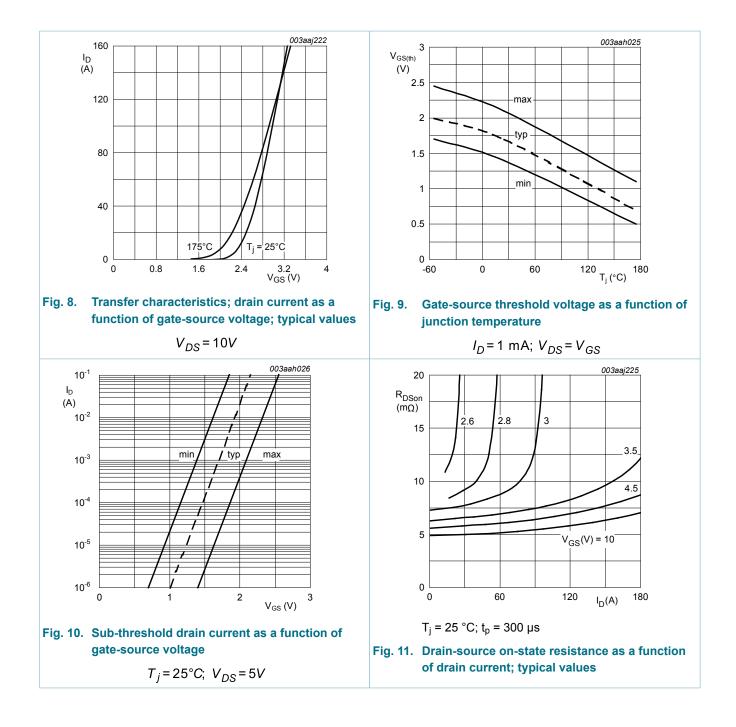
V_{DS} = 25 V; T_i = 25 °C

 $T_j = 25^{\circ}C; I_D = 25A$

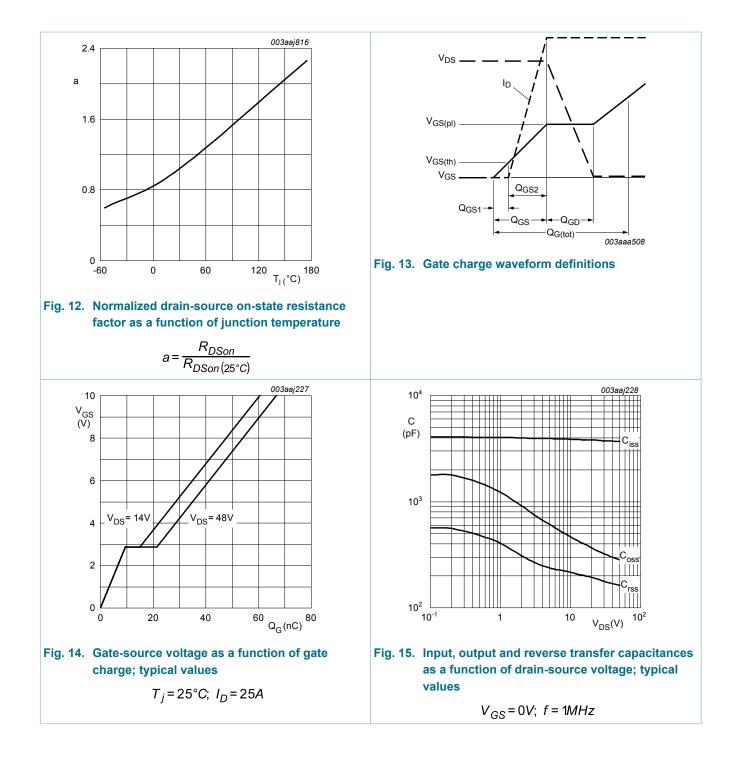
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N-channel 60 V, 5.6 mΩ logic level MOSFET in LFPAK56

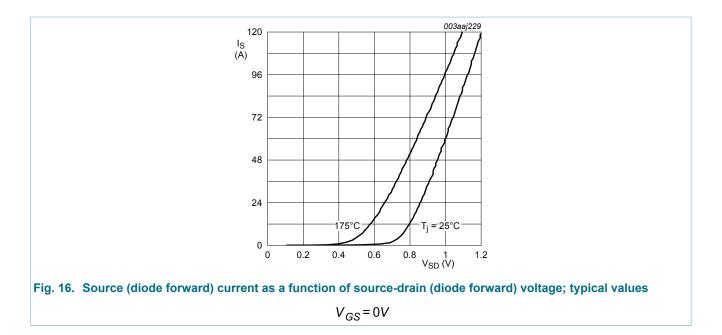


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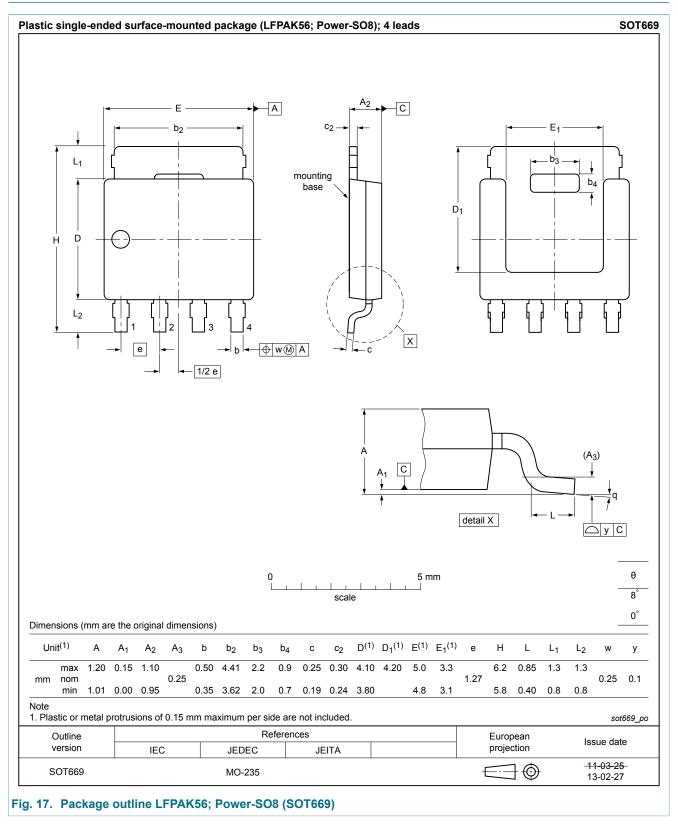
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11. Package outline



PSMN5R6-60YL

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12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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N-channel 60 V, 5.6 mΩ logic level MOSFET in LFPAK56

13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Package outline	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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